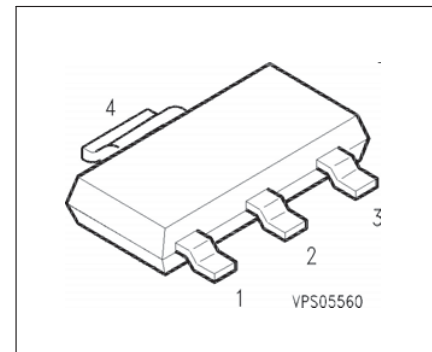
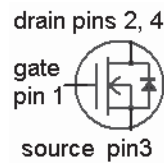


SIPMOS® Small-Signal Transistor

- N channel
- Enhancement mode
- Logic Level
- Avalanche rated
- $V_{GS(th)} = 0.8 \dots 2.0 \text{ V}$
- Pb-free lead plating; RoHS compliant
- Qualified according to AEC Q101



| Pin 1 | Pin 2 | Pin 3 | Pin 4 |
|-------|-------|-------|-------|
| G | D | S | D |

| Type | V_{DS} | I_D | $R_{DS(on)}$ |
|--------|----------|-------|---------------|
| BSP372 | 100 V | 1.7 A | 0.31 Ω |

| Type | Package | Tape and Reel Information | Marking | Packaging |
|--------|-----------|---------------------------|---------|-----------|
| BSP372 | PG-SOT223 | L6327: 1000 pcs/reel | BSP372 | Non dry |

Maximum Ratings

| Parameter | Symbol | Values | Unit |
|--|-------------|----------|------|
| Continuous drain current $T_A = 28 \text{ }^\circ\text{C}$ | I_D | 1.7 | A |
| DC drain current, pulsed $T_A = 25 \text{ }^\circ\text{C}$ | I_{Dpuls} | 6.8 | |
| Avalanche energy, single pulse $I_D = 1.7 \text{ A}$, $V_{DD} = 25 \text{ V}$, $R_{GS} = 25 \text{ } \Omega$ $L = 23.3 \text{ mH}$, $T_j = 25 \text{ }^\circ\text{C}$ | E_{AS} | 45 | mJ |
| Gate source voltage | V_{GS} | ± 14 | V |
| Gate-source peak voltage,aperiodic | V_{gs} | ± 20 | |
| Power dissipation $T_A = 25 \text{ }^\circ\text{C}$ | P_{tot} | 1.8 | W |

Maximum Ratings

| Parameter | Symbol | Values | Unit |
|--|------------|---------------|------|
| Chip or operating temperature | T_j | -55 ... + 150 | °C |
| Storage temperature | T_{stg} | -55 ... + 150 | |
| Thermal resistance, chip to ambient air ¹⁾ | R_{thJA} | ≤ 70 | K/W |
| Thermal resistance, junction-soldering point ¹⁾ | R_{thJS} | ≤ 10 | |
| IEC climatic category, DIN IEC 68-1 | | 55 / 150 / 56 | |

1) Transistor on epoxy pcb 40 mm x 40 mm x 1,5 mm with 6 cm² copper area for drain connection

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Values | | | Unit |
|-----------|--------|--------|------|------|------|
| | | min. | typ. | max. | |

Static Characteristics

| | | | | | |
|--|---------------|-----|-----------|----------|----|
| Drain- source breakdown voltage $V_{GS} = 0\text{ V}, I_D = 0.25\text{ mA}, T_j = 0^\circ\text{C}$ | $V_{(BR)DSS}$ | 100 | - | - | V |
| Gate threshold voltage $V_{GS} = V_{DS}, I_D = 1\text{ mA}$ | $V_{GS(th)}$ | 0.8 | 1.4 | 2 | |
| Zero gate voltage drain current $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_j = 25^\circ\text{C}$ $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_j = 125^\circ\text{C}$ | I_{DSS} | - | 0.1 10 | 1 100 | μA |
| Gate-source leakage current $V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$ | I_{GSS} | - | 10 | 100 | |
| Drain-Source on-state resistance $V_{GS} = 5\text{ V}, I_D = 1.7\text{ A}$ | $R_{DS(on)}$ | - | 0.24 | 0.31 | Ω |

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

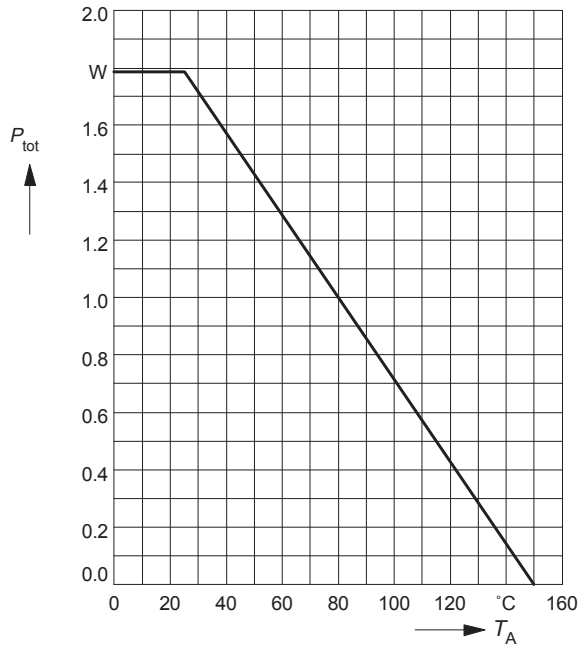
| Parameter | Symbol | Values | | | Unit |
|--|--------------|--------|------|------|------|
| | | min. | typ. | max. | |
| Dynamic Characteristics | | | | | |
| Transconductance $V_{DS} \geq 2 * I_D * R_{DS(on)max}$, $I_D = 1.7\text{ A}$ | g_{fs} | 2 | 3.7 | - | S |
| Input capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$ | C_{iss} | - | 415 | 520 | pF |
| Output capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$ | C_{oss} | - | 80 | 100 | |
| Reverse transfer capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$ | C_{rss} | - | 50 | 65 | |
| Turn-on delay time $V_{DD} = 30\text{ V}$, $V_{GS} = 5\text{ V}$, $I_D = 0.3\text{ A}$ $R_G = 50\ \Omega$ | $t_{d(on)}$ | - | 20 | 30 | ns |
| Rise time $V_{DD} = 30\text{ V}$, $V_{GS} = 5\text{ V}$, $I_D = 0.3\text{ A}$ $R_G = 50\ \Omega$ | t_r | - | 35 | 55 | |
| Turn-off delay time $V_{DD} = 30\text{ V}$, $V_{GS} = 5\text{ V}$, $I_D = 0.3\text{ A}$ $R_G = 50\ \Omega$ | $t_{d(off)}$ | - | 110 | 165 | |
| Fall time $V_{DD} = 30\text{ V}$, $V_{GS} = 5\text{ V}$, $I_D = 0.3\text{ A}$ $R_G = 50\ \Omega$ | t_f | - | 50 | 75 | |

Electrical Characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Values | | | Unit |
|---|----------|--------|------|------|---------------|
| | | min. | typ. | max. | |
| Reverse Diode | | | | | |
| Inverse diode continuous forward current $T_A = 25^\circ\text{C}$ | I_S | - | - | 1.7 | A |
| Inverse diode direct current, pulsed $T_A = 25^\circ\text{C}$ | I_{SM} | - | - | 6.8 | |
| Inverse diode forward voltage $V_{GS} = 0\text{ V}, I_F = 1.7\text{ A}$ | V_{SD} | - | 0.85 | 1.1 | V |
| Reverse recovery time $V_R = 30\text{ V}, I_F = I_S, di_F/dt = 100\text{ A}/\mu\text{s}$ | t_{rr} | - | 65 | - | ns |
| Reverse recovery charge $V_R = 30\text{ V}, I_F = I_S, di_F/dt = 100\text{ A}/\mu\text{s}$ | Q_{rr} | - | 0.11 | - | μC |

Power dissipation

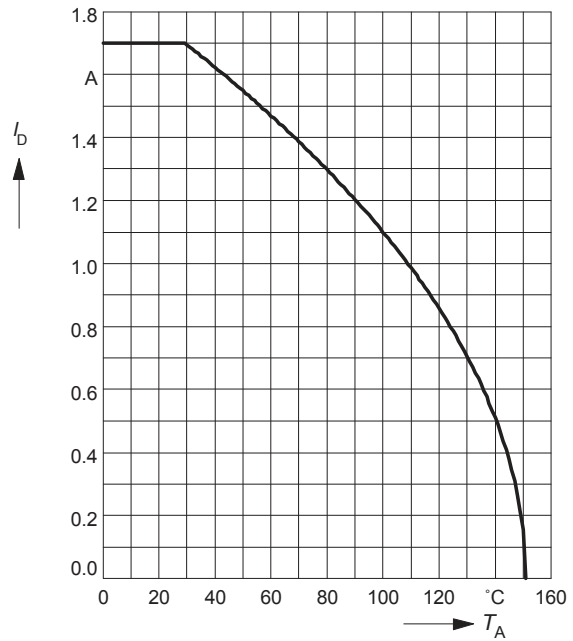
$P_{tot} = f(T_A)$



Drain current

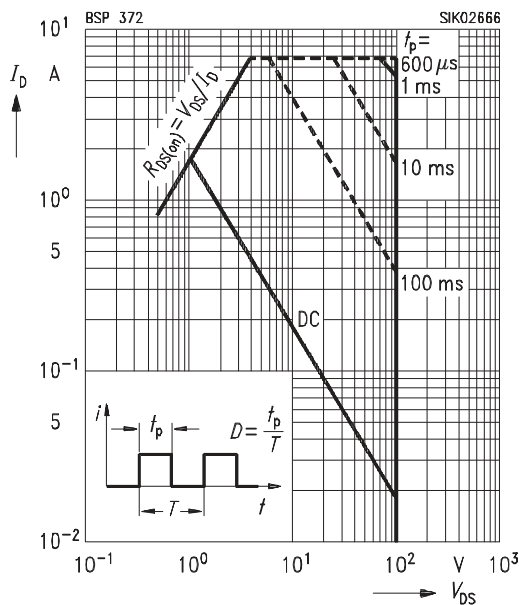
$I_D = f(T_A)$

parameter: $V_{GS} \geq 5 \text{ V}$



Safe operating area $I_D = f(V_{DS})$

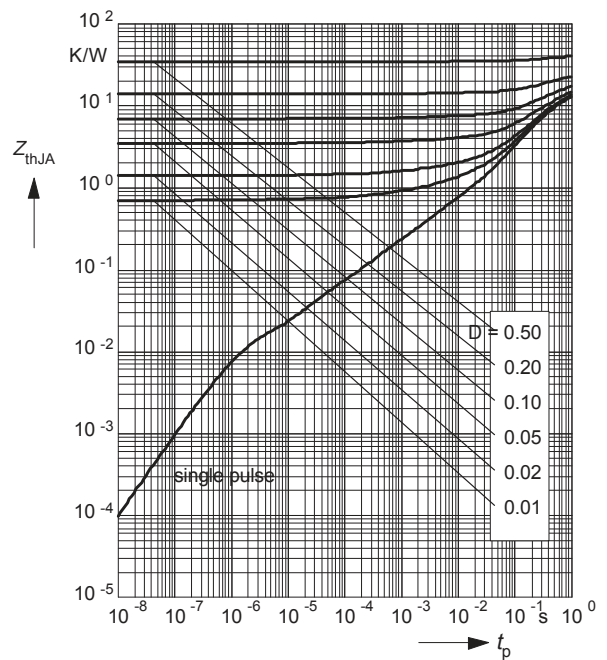
parameter: $D = 0, T_C = 25^\circ\text{C}$



Transient thermal impedance

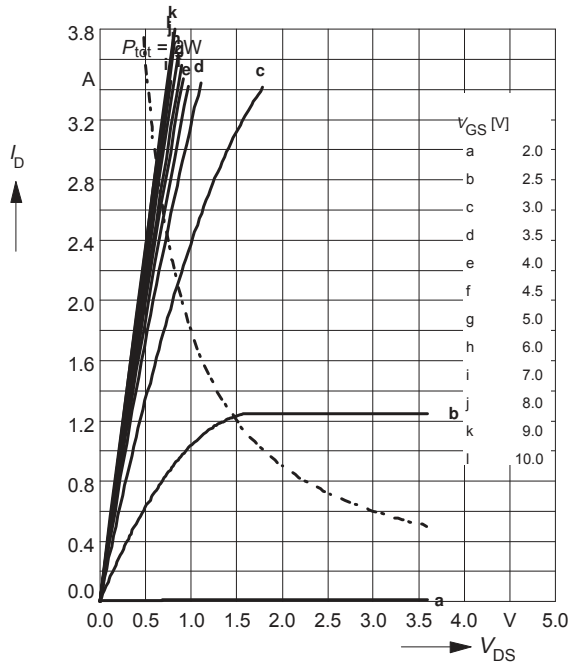
$Z_{thJA} = f(t_p)$

parameter: $D = t_p / T$



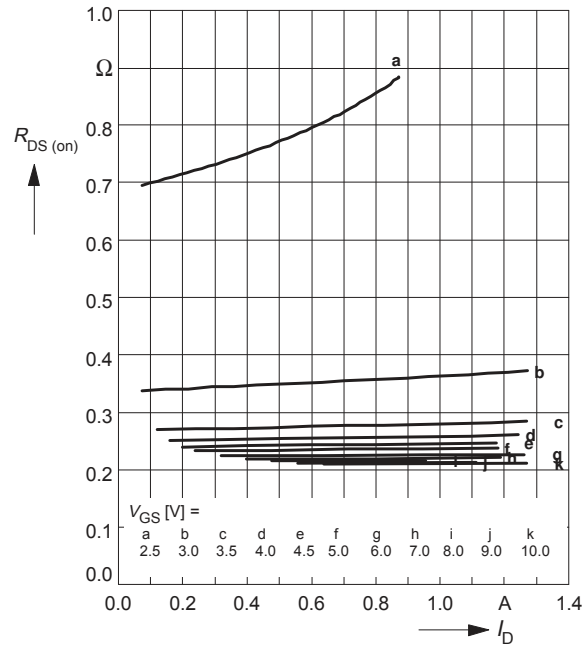
Typ. output characteristics

$I_D = f(V_{DS})$
parameter: $t_p = 80 \mu s$



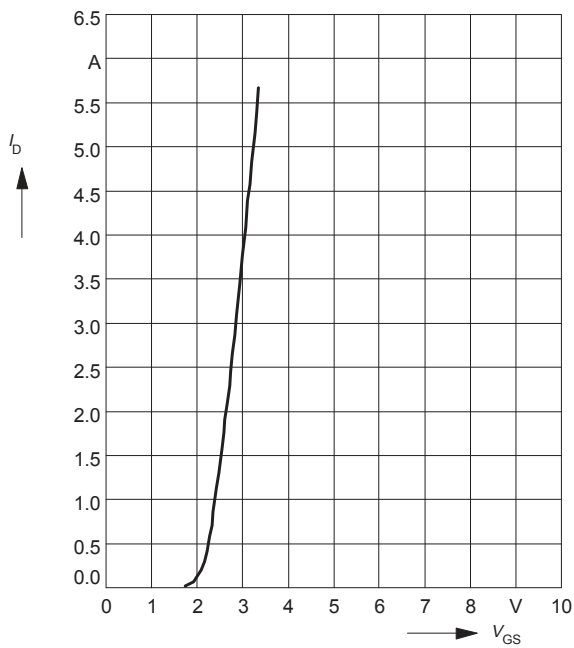
Typ. drain-source on-resistance

$R_{DS(on)} = f(I_D)$
parameter: $t_p = 80 \mu s, T_j = 25^\circ C$



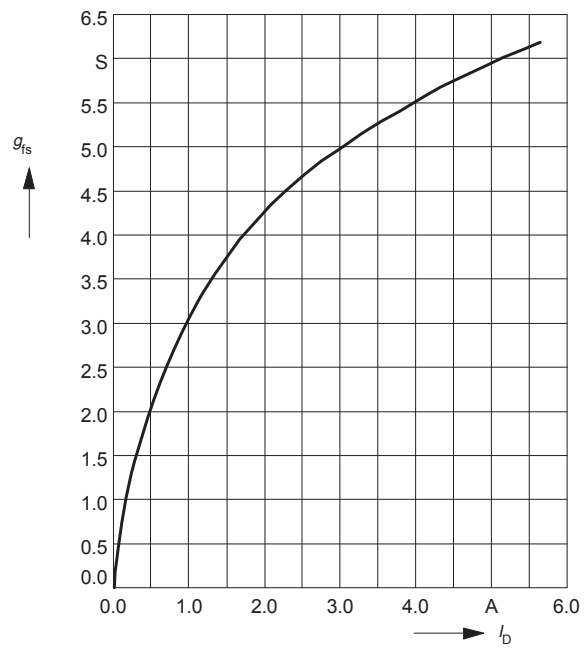
Typ. transfer characteristics $I_D = f(V_{GS})$

parameter: $t_p = 80 \mu s$
 $V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$



Typ. forward transconductance $g_{fs} = f(I_D)$

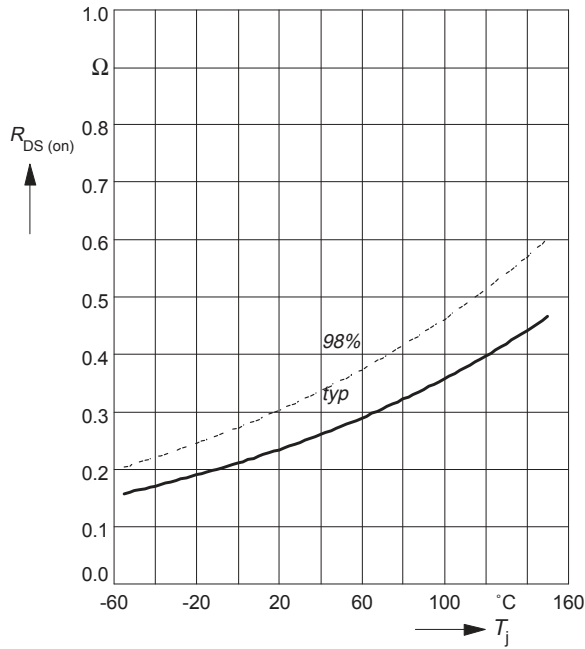
parameter: $t_p = 80 \mu s,$
 $V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$



Drain-source on-resistance

$$R_{DS(on)} = f(T_j)$$

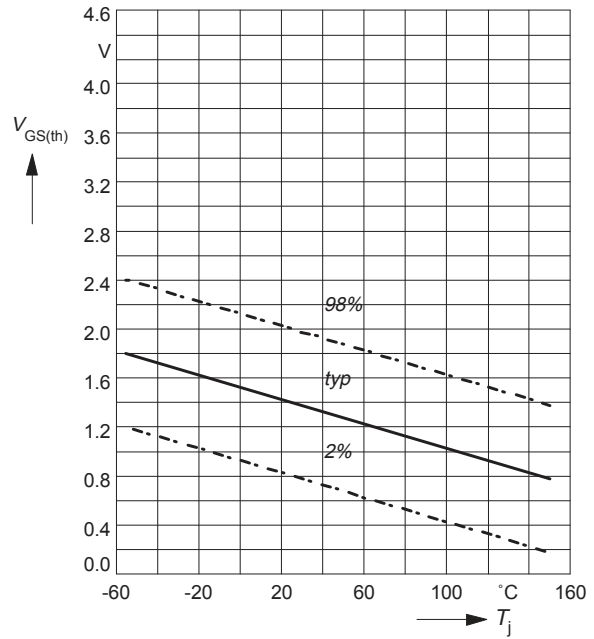
parameter: $I_D = 1.7 \text{ A}$, $V_{GS} = 5 \text{ V}$



Gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

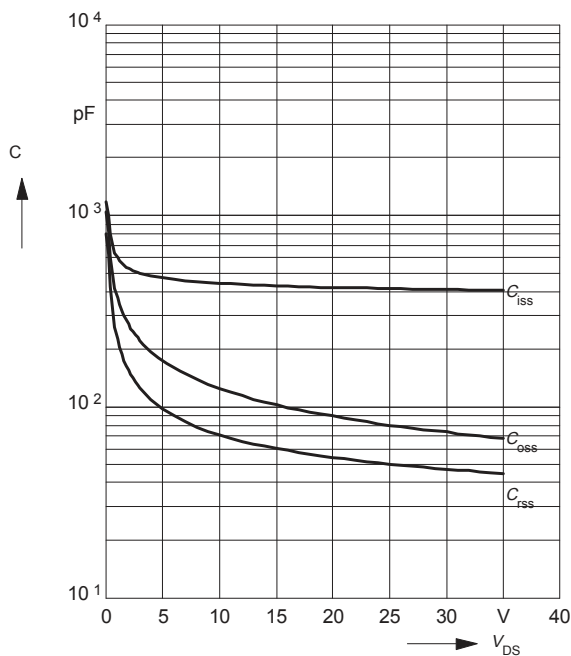
parameter: $V_{GS} = V_{DS}$, $I_D = 1 \text{ mA}$



Typ. capacitances

$$C = f(V_{DS})$$

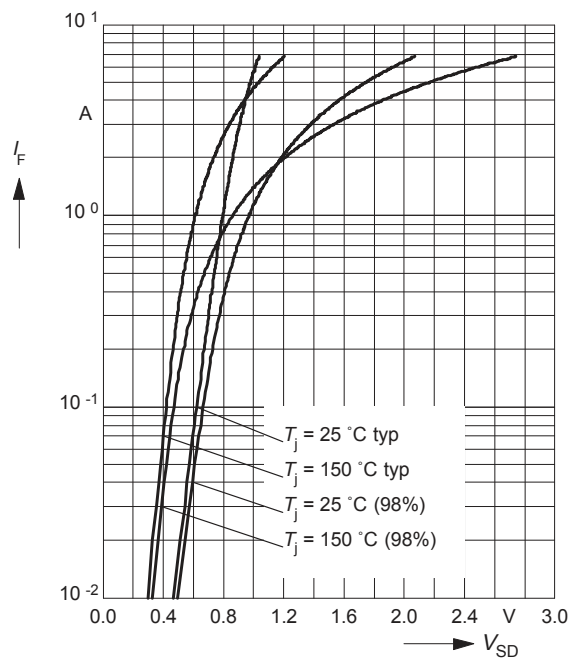
parameter: $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$



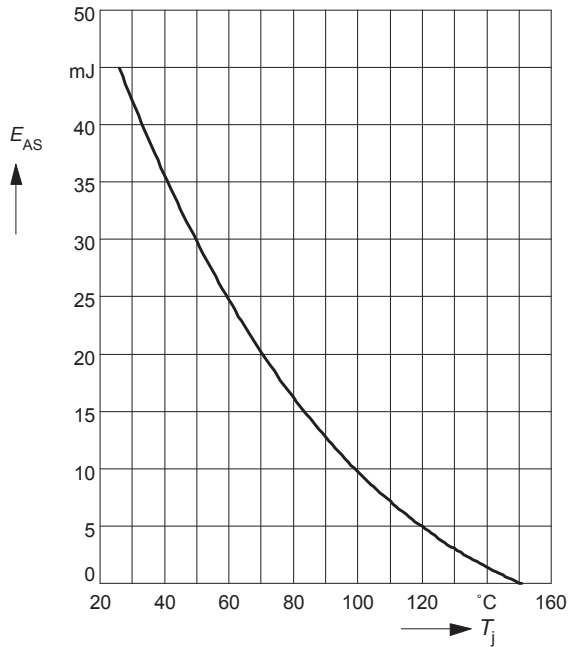
Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

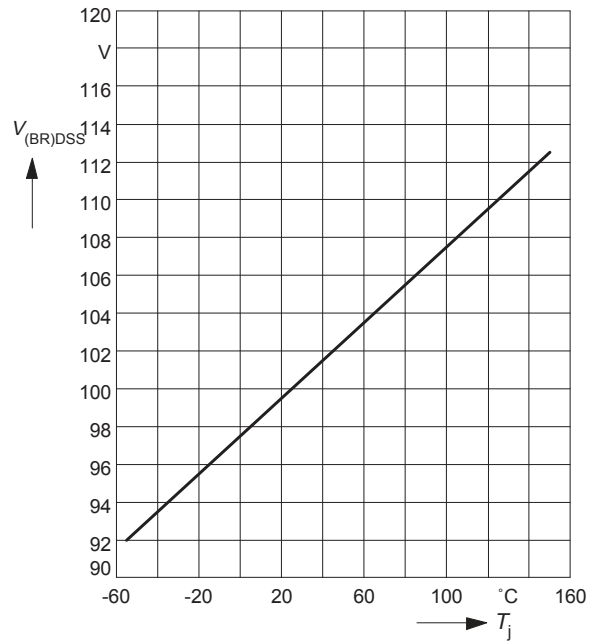
parameter: $T_j, t_p = 80 \mu\text{s}$



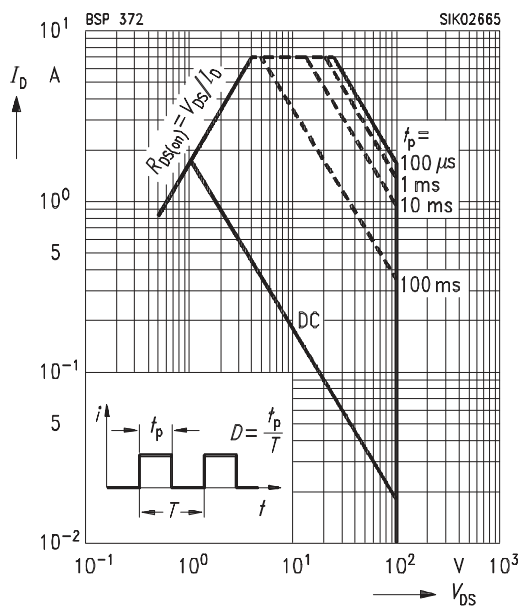
Avalanche energy $E_{AS} = f(T_j)$
 parameter: $I_D = 1.7 \text{ A}$, $V_{DD} = 25 \text{ V}$
 $R_{GS} = 25 \Omega$, $L = 23.3 \text{ mH}$



Drain-source breakdown voltage
 $V_{(BR)DSS} = f(T_j)$



Safe operating area $I_D = f(V_{DS})$
 parameter : $D = 0.01$, $T_C = 25^\circ\text{C}$



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